

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S118	606	216/27.ccls.	US-PGPUB; USPAT	OR	OFF	2007/01/24 11:47
S119	606	S118	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 11:47
S120	0	(ink fluid liquid) near (jet\$3 record\$3 eject\$3 discharge\$3) near head same (heater resistor) same insulating near layer same partial near etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 11:49
S121	3	(heater resistor) same insulating near layer same partial near etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 11:50
S122	3	"257"/\$.ccls. and (heater resistor) same insulating near layer same partial near etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 11:52
S123	0	S119 and (heater\$3 resistor\$3) near (element device) same insulating near layer same partial near etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 11:53
S124	0	(heater\$3 resistor\$3) near (element device) same insulating near layer same partial near etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 11:53
S125	937	29/611.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 14:45

EAST Search History

S12 6	22	("4513298" "4590482" "4602421" "4809428" "4847674" "4990939" "5159353" "5159430" "5194877" "5232865" "5330930" "5459501" "5500553" "5744846" "5870121" "5883650" "5943076" "5981329" "5998276" "6008082" "6079811" "6227640").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/24 15:47
S12 7	22	("4513298" "4590482" "4602421" "4809428" "4847674" "4990939" "5159353" "5159430" "5194877" "5232865" "5330930" "5459501" "5500553" "5744846" "5870121" "5883650" "5943076" "5981329" "5998276" "6008082" "6079811" "6227640").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/24 15:51
S12 8	1	("6785956").URPN.	USPAT	OR	ON	2007/01/24 16:01
S12 9	205	(substrate wafer chip base) same insulating near layer same protruding near portion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:31
S13 0	35	S129 and (flank\$3 side) near portion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:29
S13 1	3	insulating near layer with protruding near portion with (flank\$3 side) near portion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:32
S13 2	606	216/27.ccls.	US-PGPUB; USPAT	OR	OFF	2007/01/24 16:33
S13 3	606	S132	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:33

EAST Search History

S13 4	606	S133	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:34
S13 5	0	(substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion same vertical near sidewall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:35
S13 6	0	S134 and (substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion same vertical near sidewall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:36
S13 7	0	S134 and (substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:36
S13 8	0	S134 and (substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion.clm.	US-PGPUB	OR	ON	2007/01/24 16:43
S13 9	336	347/204-208.ccls.	US-PGPUB; USPAT	OR	OFF	2007/01/24 16:37
S14 0	336	S139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:37
S14 1	1653	347/56,61-62,67,87.ccls.	US-PGPUB; USPAT	OR	OFF	2007/01/24 16:39
S14 2	1653	S141	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:40
S14 3	301	438/21.ccls.	US-PGPUB; USPAT	OR	OFF	2007/01/24 16:41

EAST Search History

S14 4	301	S143	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:41
S14 5	937	29/611.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:42
S14 6	937	S145	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:42
S14 7	0	S140 and (substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion.clm.	US-PGPUB	OR	ON	2007/01/24 16:43
S14 8	0	S141 and (substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion.clm.	US-PGPUB	OR	ON	2007/01/24 16:43
S15 0	0	S144 and (substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion.clm.	US-PGPUB	OR	ON	2007/01/24 16:43
S15 1	0	S145 and (substrate wafer base chip) same insulating near layer same partial near etch\$3 same protruding near portion.clm.	US-PGPUB	OR	ON	2007/01/24 16:44
S15 2	709	347/61-62.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:44
S15 3	709	S152	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:44

EAST Search History

S15 4	0	S153 and (heater resistor) same insulating near layer same partial near etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/24 16:45
S15 5	0	S153 and (heater resistor) same insulating near layer same partial near etch\$3.clm.	US-PGPUB	OR	ON	2007/01/24 16:46
S15 6	0	S139 and (heater resistor) same insulating near layer same partial near etch\$3.clm.	US-PGPUB	OR	ON	2007/01/24 16:46
S15 7	0	S142 and (heater resistor) same insulating near layer same partial near etch\$3.clm.	US-PGPUB	OR	ON	2007/01/24 16:46
S15 8	0	S144 and (heater resistor) same insulating near layer same partial near etch\$3.clm.	US-PGPUB	OR	ON	2007/01/24 16:46
S15 9	0	S146 and (heater resistor) same insulating near layer same partial near etch\$3.clm.	US-PGPUB	OR	ON	2007/01/24 16:46